



# Pixel detector



*Sezione di Torino*

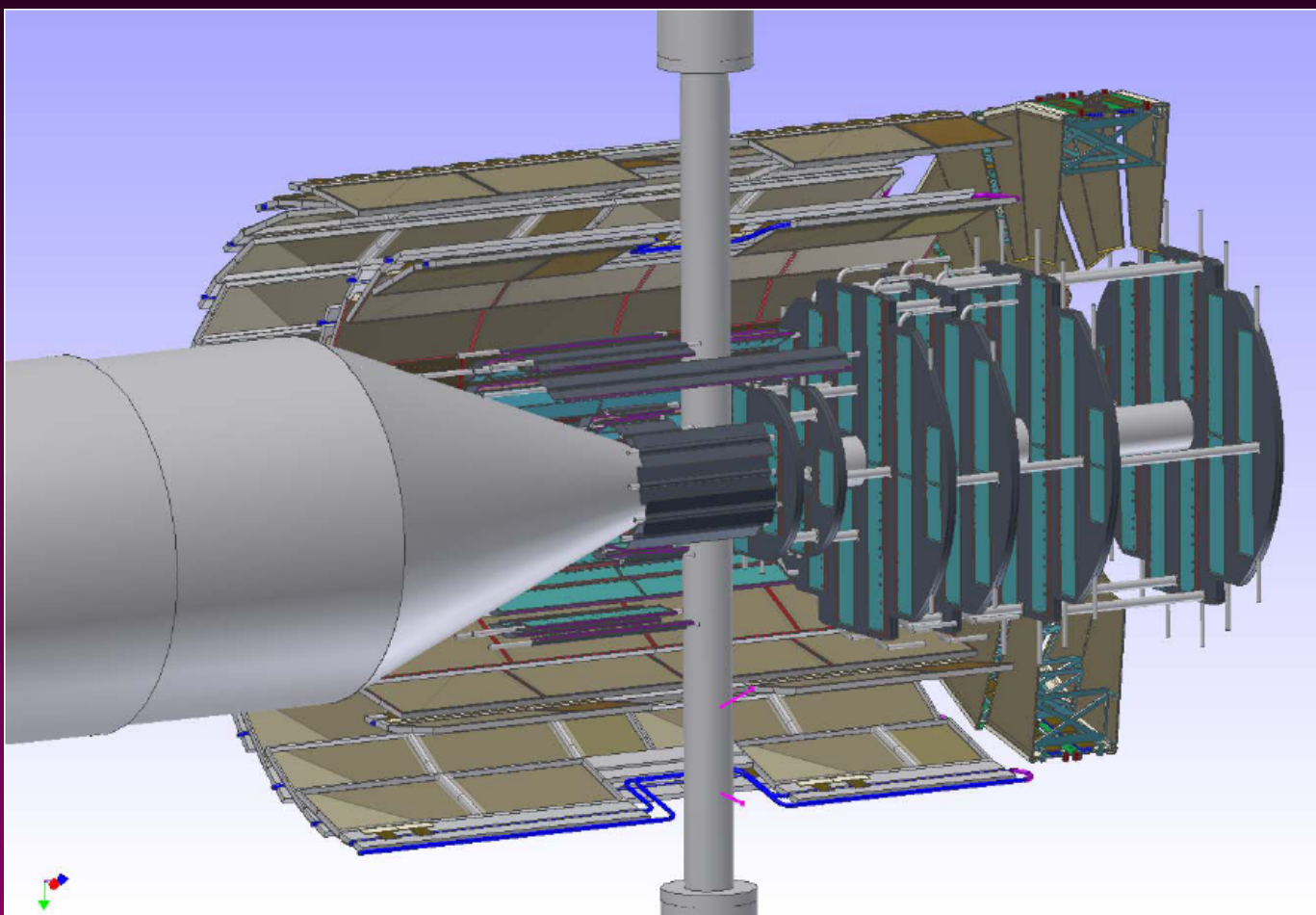
## PANDA Micro Vertex Detector pixel readout architecture



# PANDA MVD



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## \* Barrel :

Layer 1 : radius 28 mm, SPDs

Layer 2 : radius 53 mm, SPDs

Layer 3 : radius 92 mm, SSDs

Layer 4 : radius 120 mm, SSDs

## \* Forward :

Disks 1-2 : radius 37.5 mm, SPDs

Disks 3-4 : radius 75 mm, SPDs

Disks 5-6 : radius 130 mm, SPDs  
+ SSDs



# Pixel specs



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Pixel size	$100 \times 100 \mu\text{m}^2$
Chip active area	$11.4 \times 11.6 \text{ mm}^2$ (116 rows, 110 cols)
dE/dx measurement	ToT, 12 bits dynamic range
Max input charge	50 fC
Noise floor	$< 32 \text{ aC}$ (200 $e^-$ )
Clock frequency	155.52 MHz
Time resolution	6.45 ns ( 1.9 ns <i>r.m.s.</i> )
Power consumption	$< 500 \text{ mW/cm}^2$
Max event rate	<i>see next slide</i>
Total ionizing dose	$< 100 \text{ kGy}$



# Data rates (worst case scenario)



antiproton-	proton (disk)	Au (barrel)
Particle rate per $\text{cm}^2 \cdot \text{s}$	$6 \cdot 10^6$	$1.6 \cdot 10^6$
Data rates per $\text{cm}^2$ (per chip ) [Mb/s] :		
no multiple hit ( <i>avg</i> )	300 (397)	80 (110)
multiple hits, 100 $\mu\text{m}$ sensor ( <i>avg</i> )	450 (595)	120 (160)
multiple hits, 200 $\mu\text{m}$ sensor ( <i>avg</i> )	750 (992)	200 (260)
multiple hits, 100 $\mu\text{m}$ sensor ( <i>max</i> )	675 (893)	180 (240)
multiple hits, 200 $\mu\text{m}$ sensor ( <i>max</i> )	1125 (1488)	300 (398)

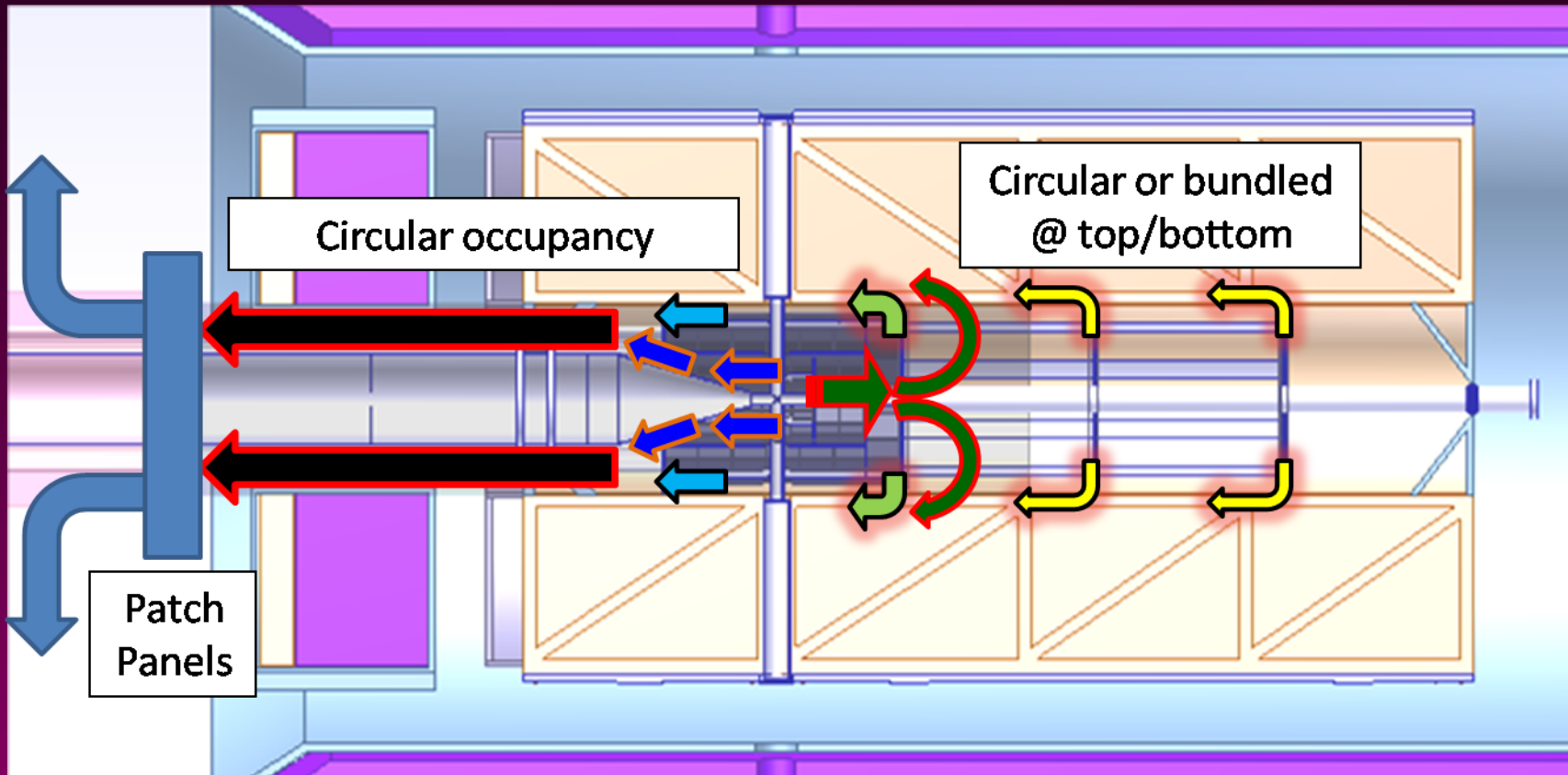
Chip sensitive area :  $1.32 \text{ cm}^2$

Avg rate :  $20 \cdot 10^6$  annihilations/s

Max rate :  $30 \cdot 10^6$  annihilations/s

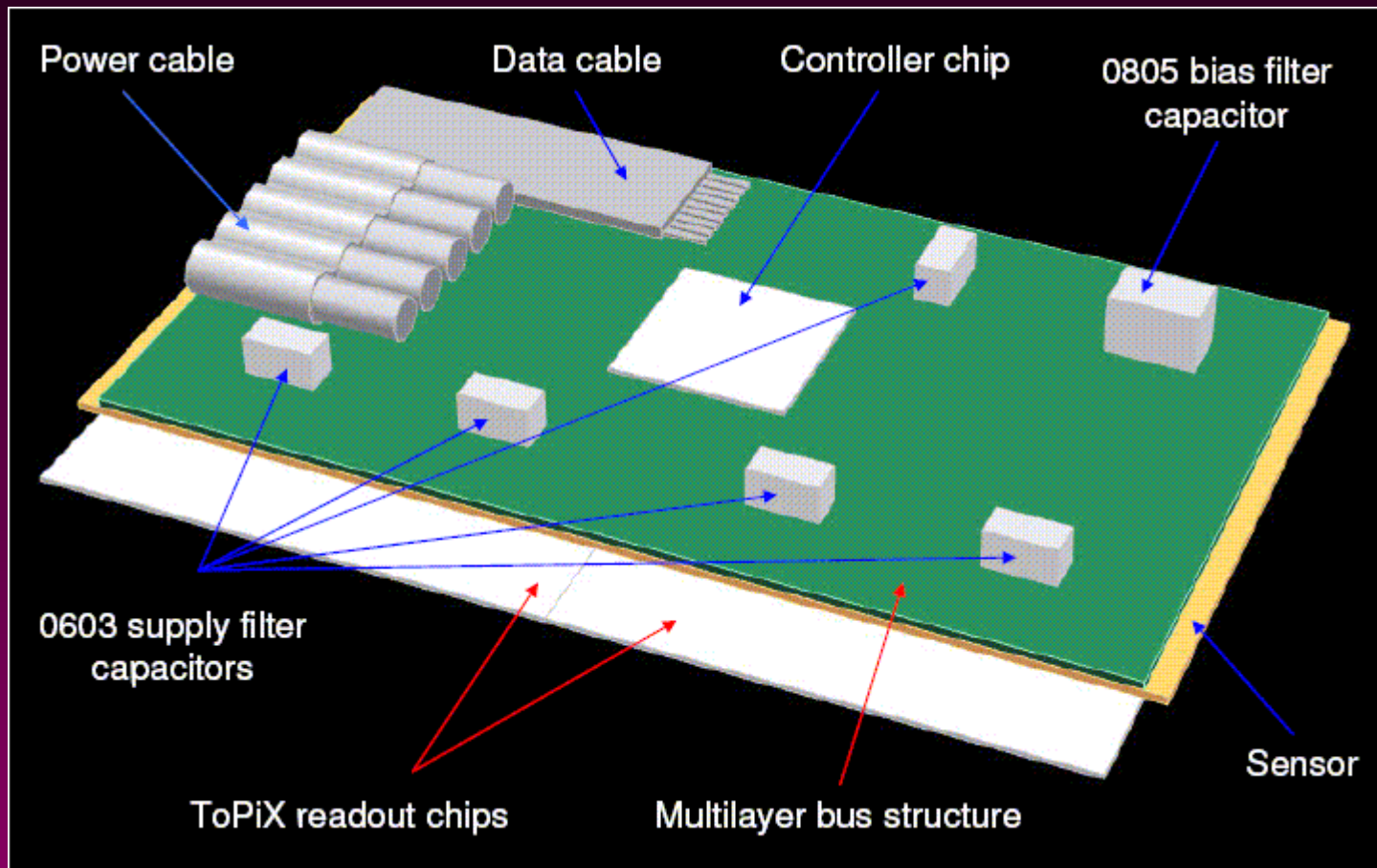


# Routing direction





# Module concept



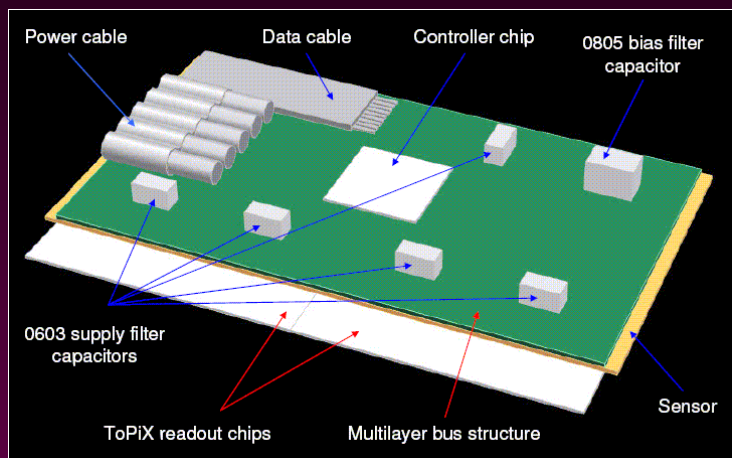




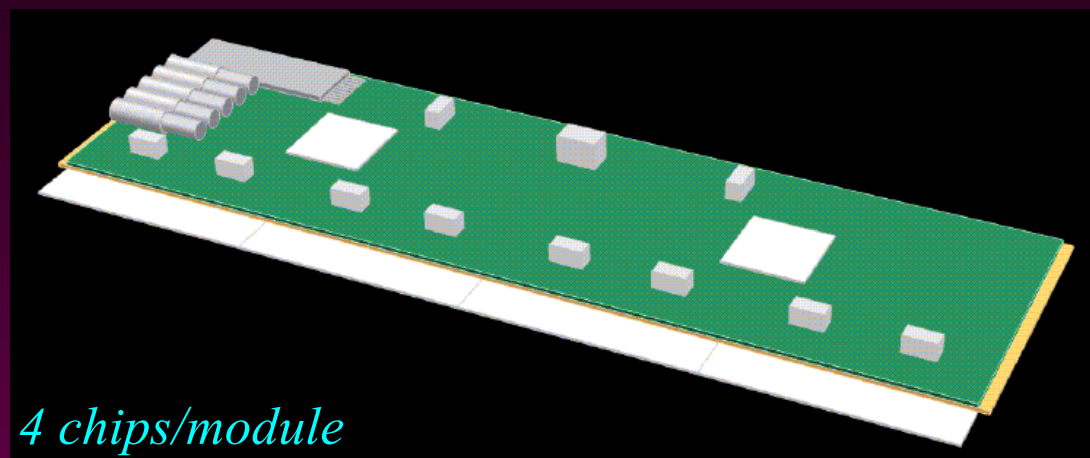
# Module types



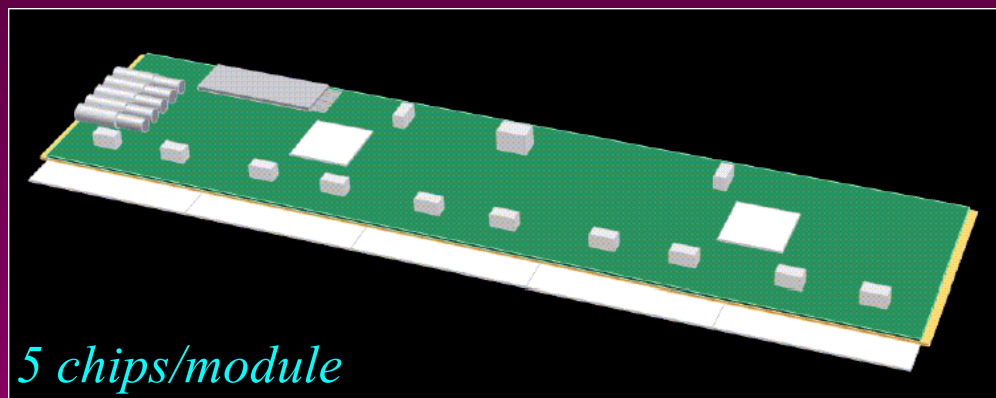
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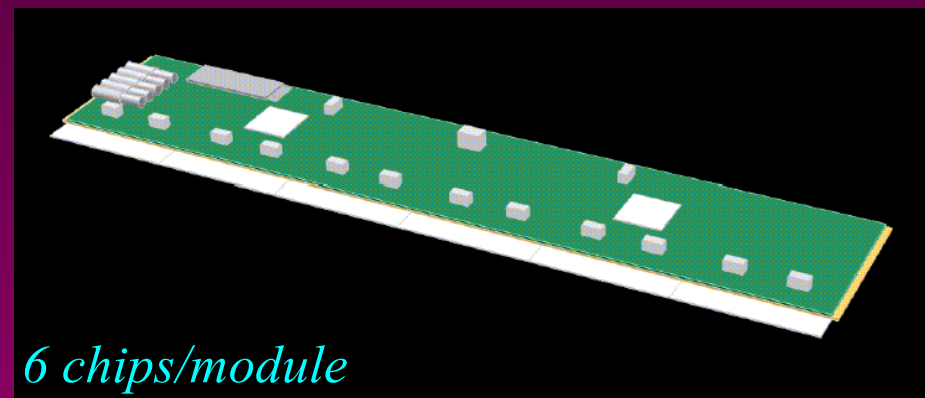
*2 chips/module*



*4 chips/module*

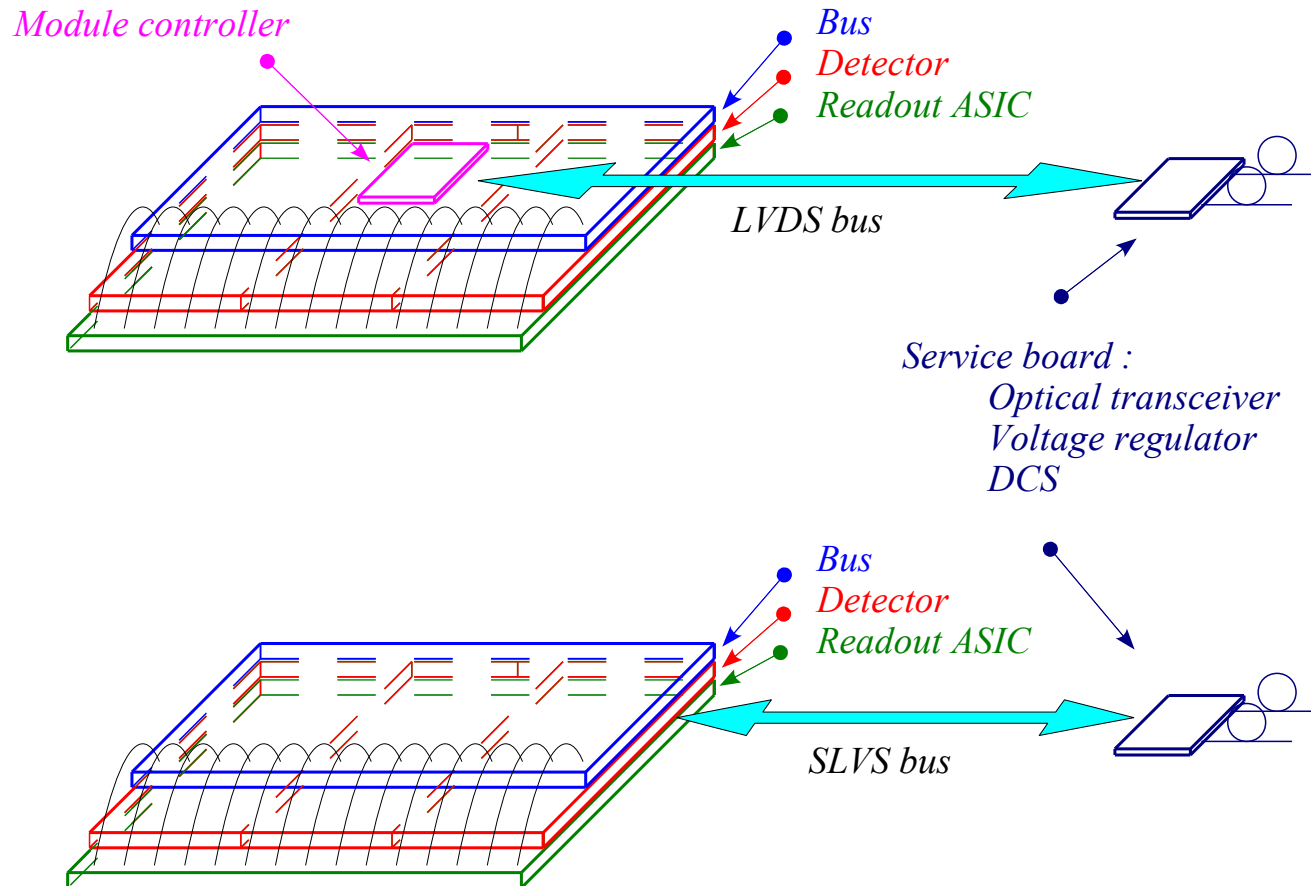


*5 chips/module*



*6 chips/module*

# Readout scheme



Option 1

Option 2





# Readout options



## \* Option 1

- ☺ reduced number of cables
- ☺ simpler ToPiX control logic
- ☺ better management of data rate increase
- ☹ requires an extra chip

## \* Option 2

- ☺ no need of an extra chip
- ☺ interface already under development at CERN
- ☹ more cables

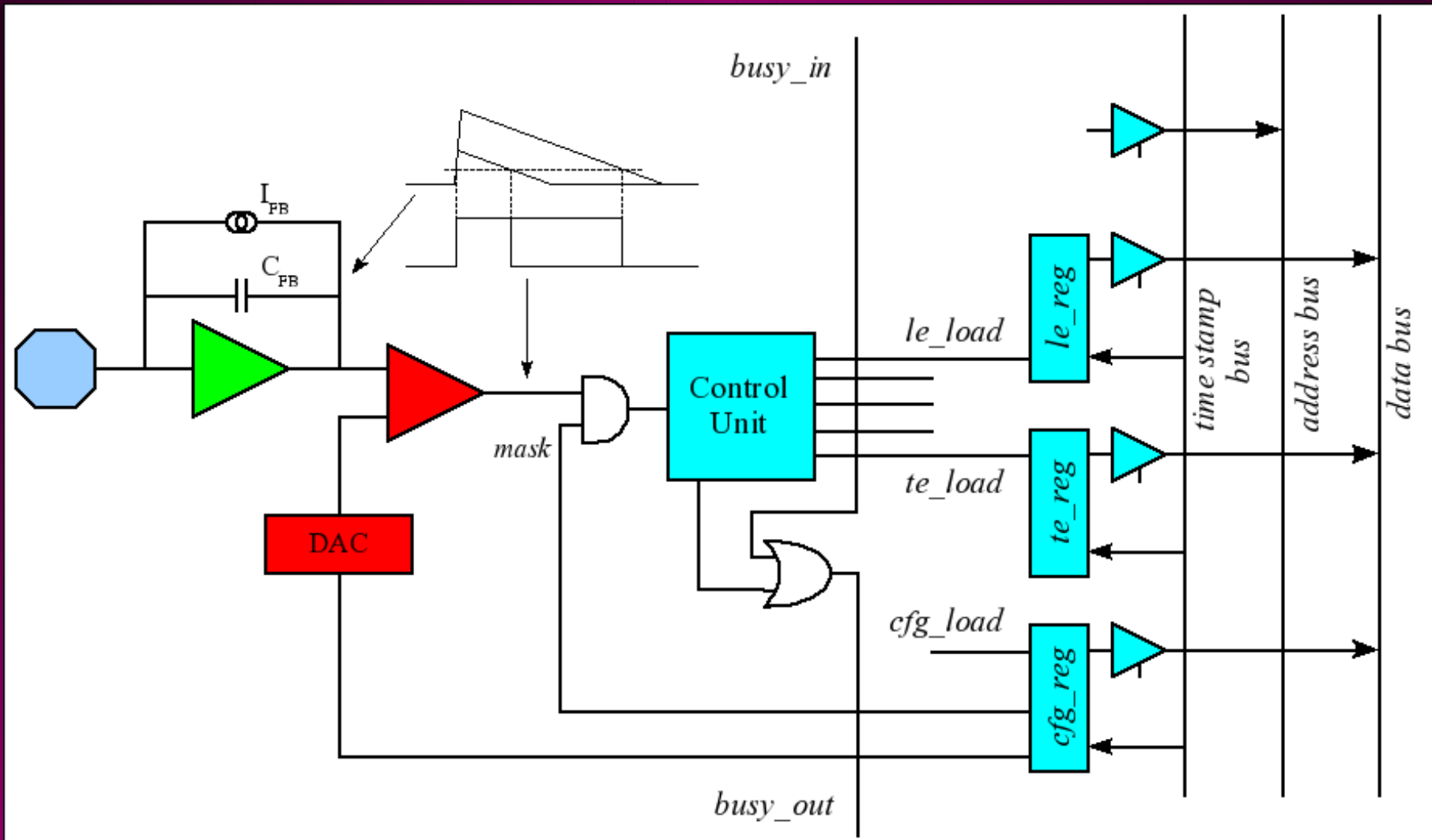


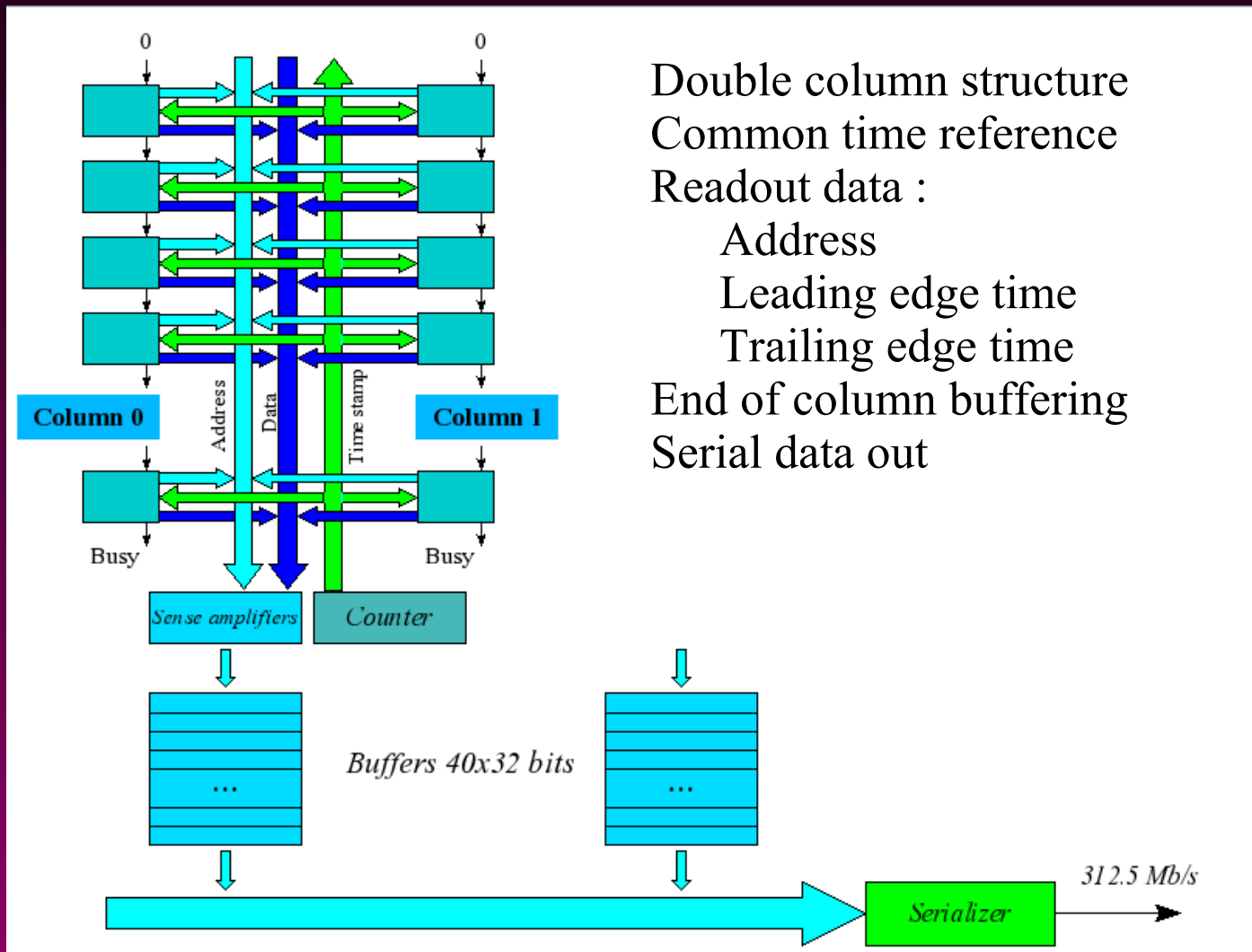
## ToPiX ASIC



- \* Custom development for the PANDA MVD
- \* Provides spatial and time coordinates plus energy resolution measurement ( via ToT )
- \* Compatible either with p-type or n-type detectors
- \* Self triggered architecture
- \* Each event has a 12 bits time reference
- \* Double rate serial readout
- \* Radiation tolerant
- \* Data corresponding to a 12 bits counter cycle (26.21  $\mu$ s ) are packed in a frame, with an 8 bits frame counter ( 6.71 ms cycle )

# Pixel cell





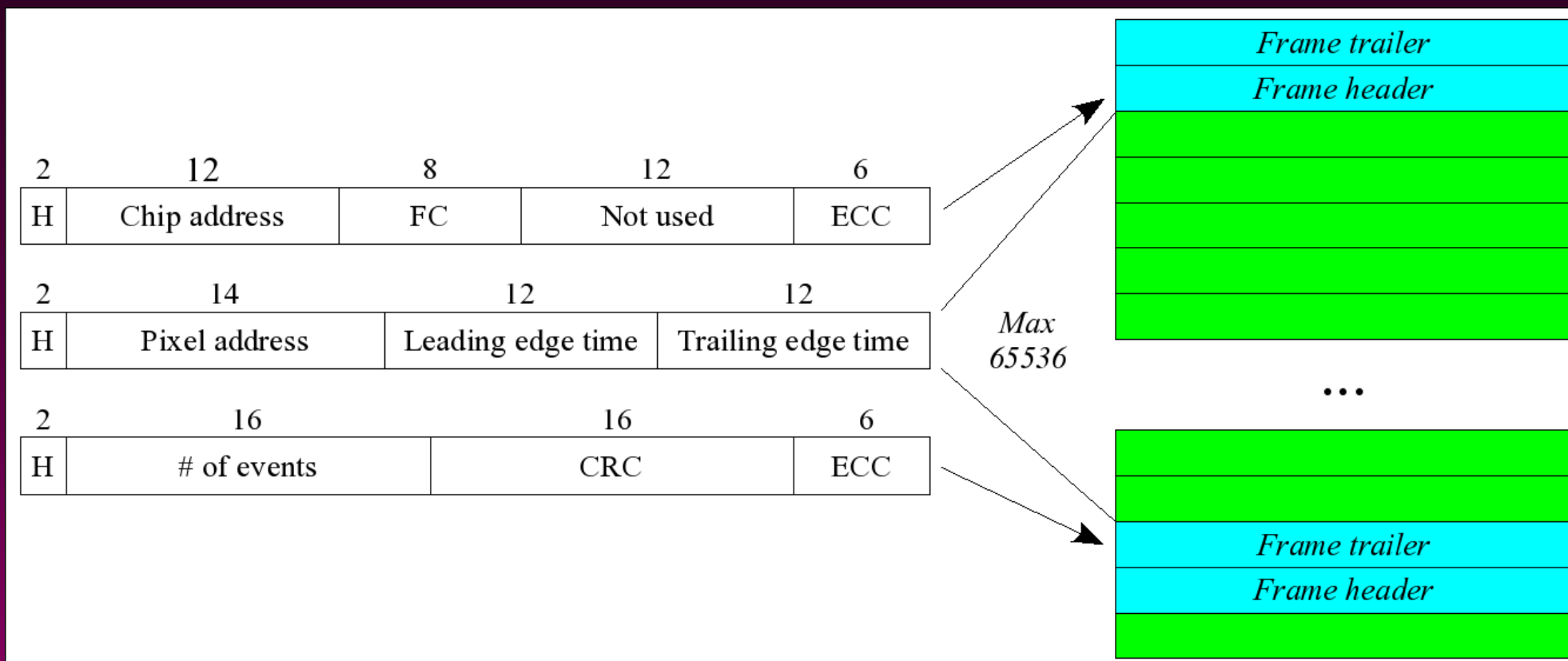
Double column structure  
 Common time reference  
 Readout data :  
 Address  
 Leading edge time  
 Trailing edge time  
 End of column buffering  
 Serial data out



# Data format

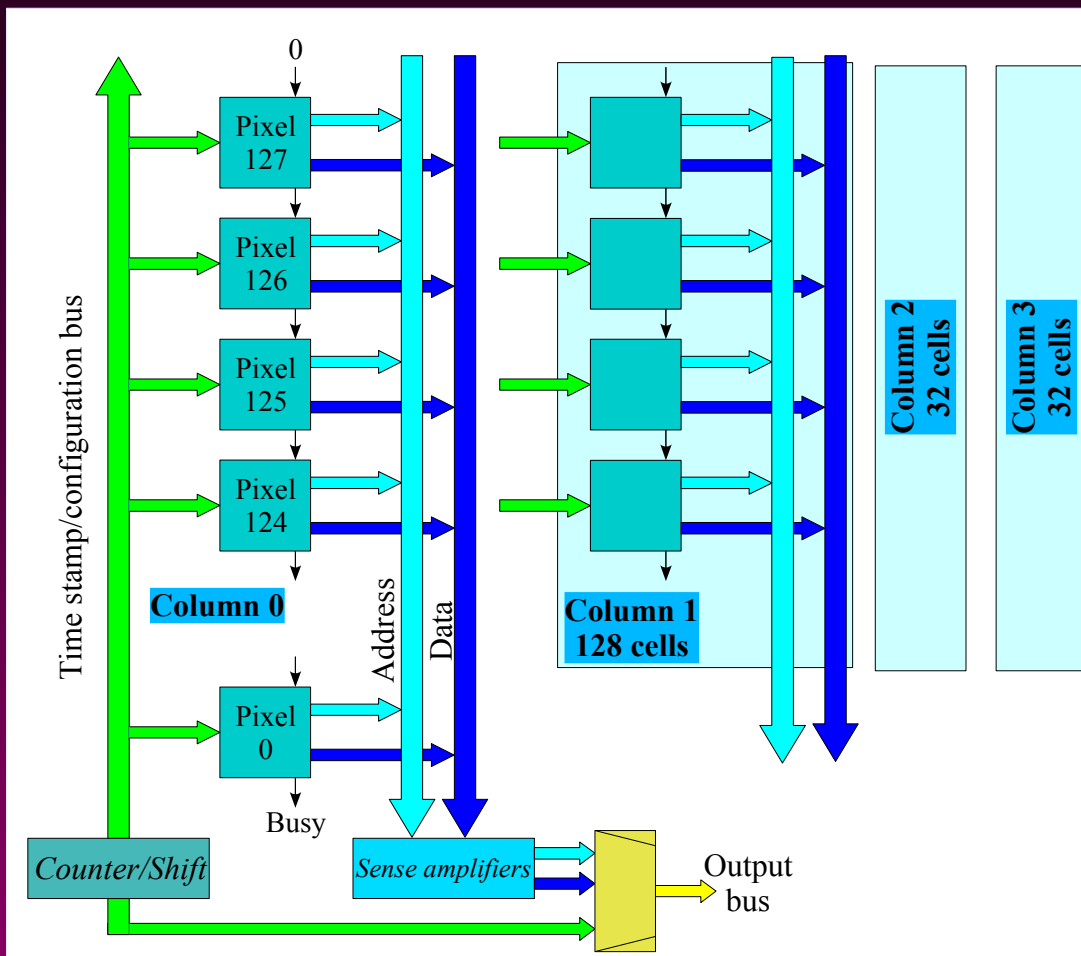


Sezione di Torino





# ToPiX v2 architecture



- Full pixel cell ( analogue + digital )
- Two folded columns with 128 cells
- Two columns with 32 cells
- $5 \times 2 \text{ mm}^2$  die area
- CMOS  $0.13 \mu\text{m}$  technology
- SEU tolerant logic (based on the DICE cell)



# ToPiX v2

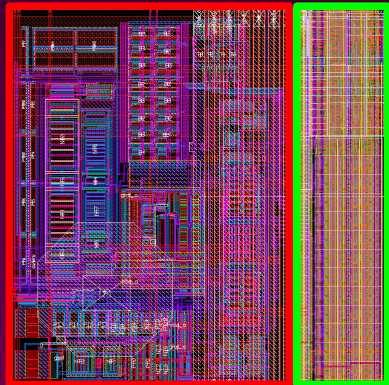


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ToPiX prototype 5 mm × 2 mm

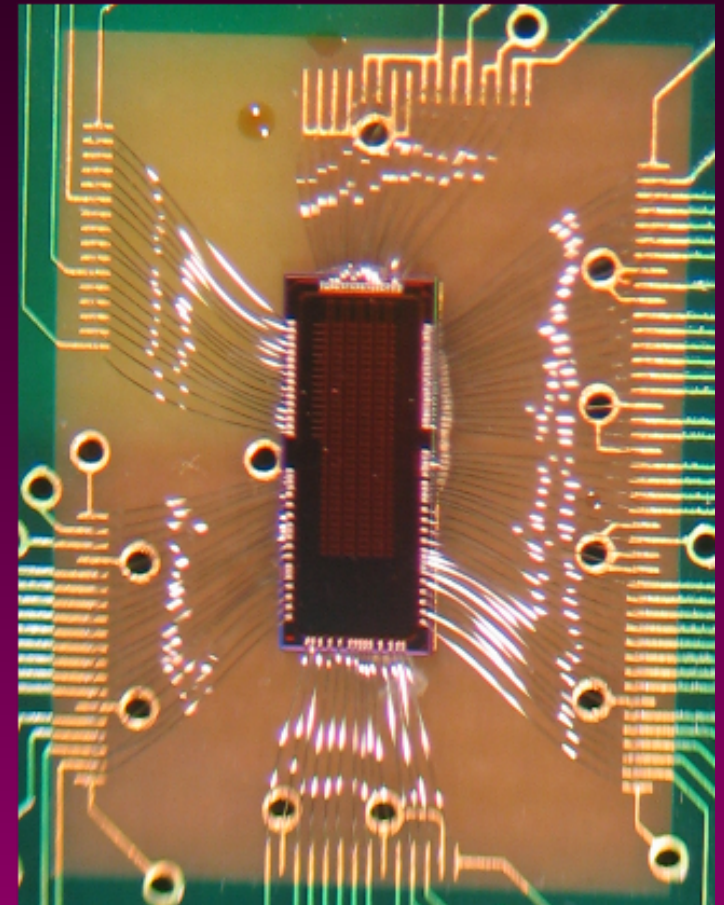
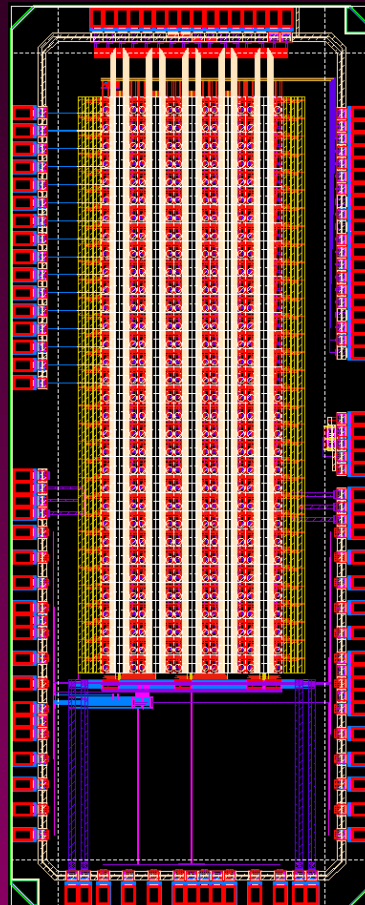
Pixel cell

100  $\mu\text{m}$  × 100  $\mu\text{m}$



Analog

Digital







## ToPiX v2



### Tests :

- \* electrical
- \* connected to a detector via wire bonding
- \* TID tests
- \* SEU tests

### References :

- D. Calvo et al, *A Silicon Pixel Readout ASIC in CMOS 0.13  $\mu\text{m}$  for the PANDA MicroVertex Detector* , Nuclear Science Symposium Conference Record, 2008 IEEE, 19-25 Oct. 2008 Page(s): 2934 – 2939
- D. Calvo et al., *The silicon pixel system for the Micro Vertex Detector of the PANDA experiment* – doi:10.1016/j.nima.2009.09.043
- T. Kugathasan, et al., *Front end electronics for pixel detector of the PANDA MVD* - Proceedings of the Topical Workshop on Electronics for Particle Physics 21-25 Sep 2009 - Paris, France - CERN 2009-006, pag. 52-56



## ToPiX v3



Sezione di Torino

- Layout submitted on February 7<sup>th</sup> – *just received*
- 4.5x4 mm<sup>2</sup> die area
- CMOS 0.13  $\mu\text{m}$  DM technology
  - LM  $\rightarrow$  6 thin, 2 thick metal layers
  - DM  $\rightarrow$  3 thin, 2 thick, 3 RF metal layers
- Triple redundancy-based SEU protection
- End of column logic
- 160 Mb/s SLVS serial output
- Pads for bump bonding



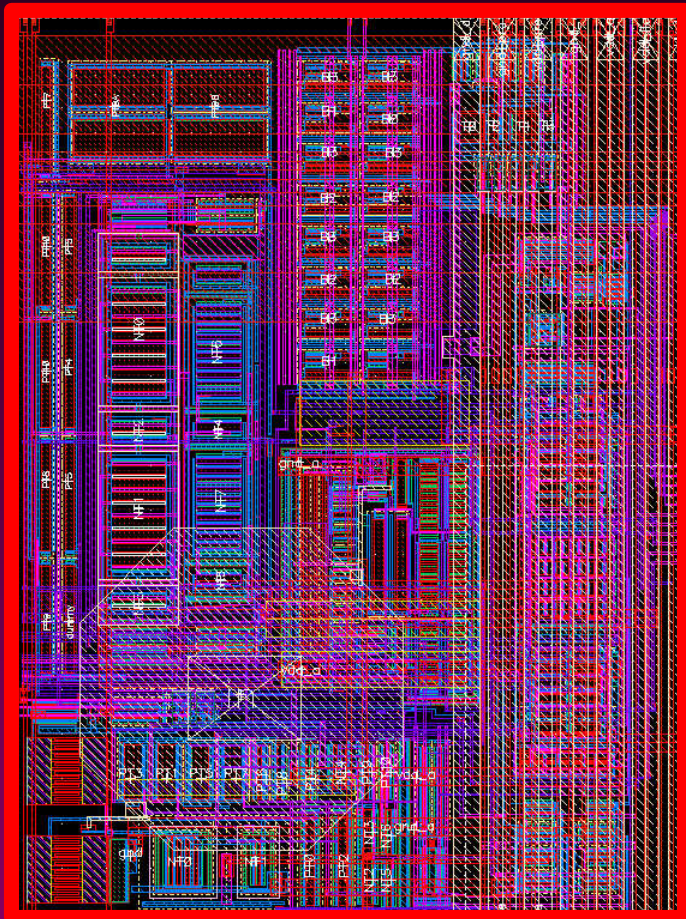


# Cell layout



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*ToPiX v2*

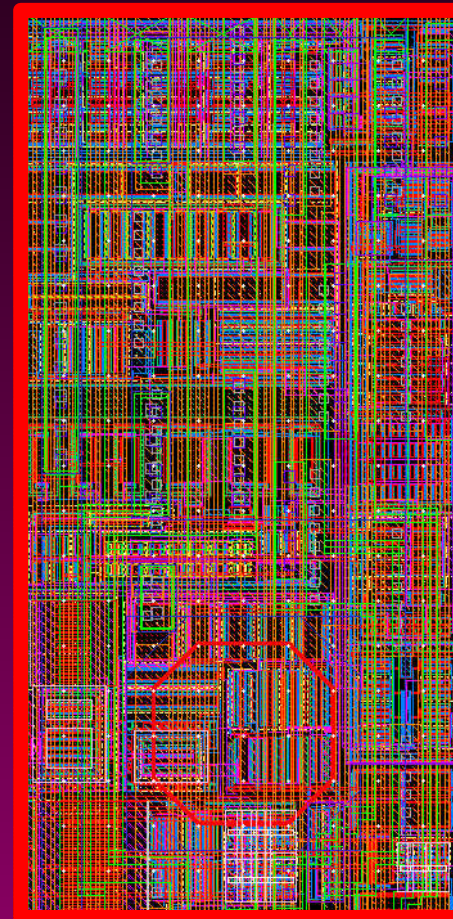


*Analogue*

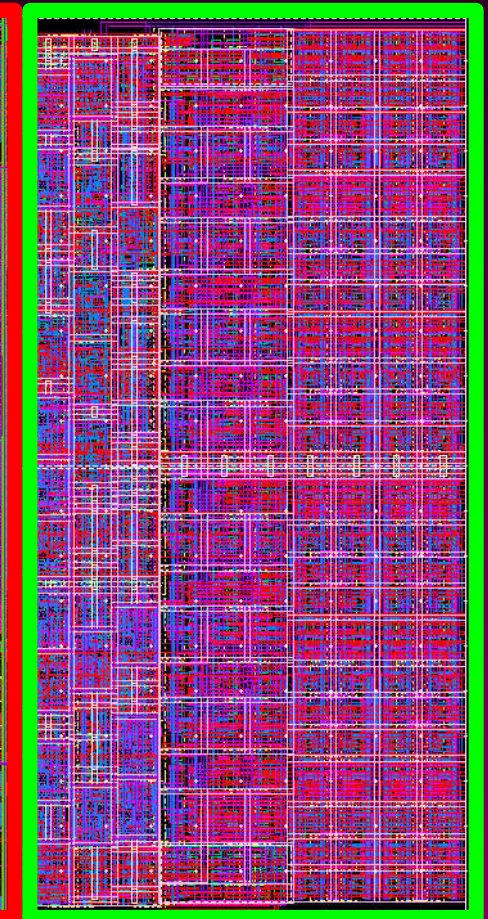


*Digital*

*ToPiX v3*



*Analogue*



*Digital*

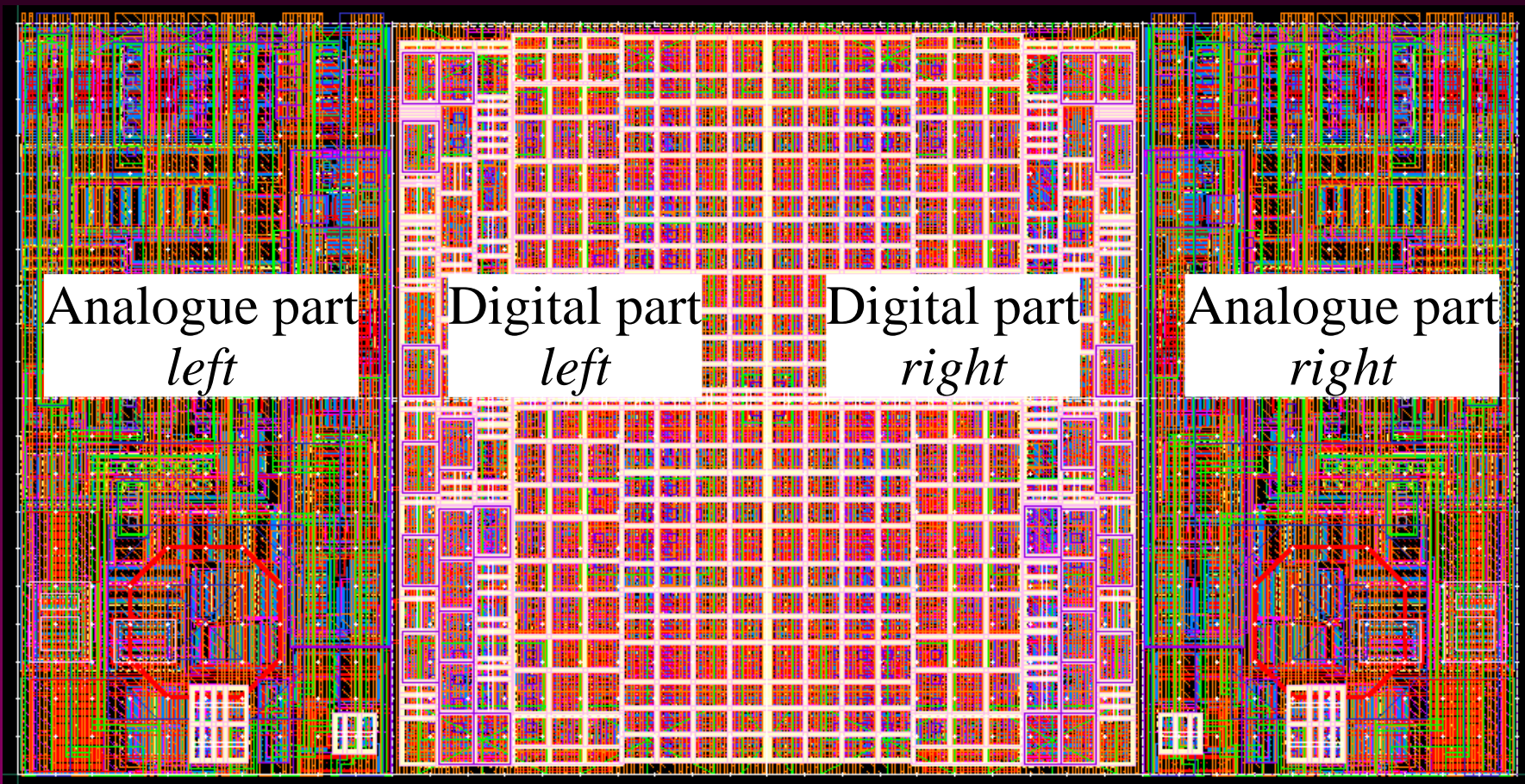




# Double cell



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Analogue part  
*left*

Digital part  
*left*

Digital part  
*right*

Analogue part  
*right*

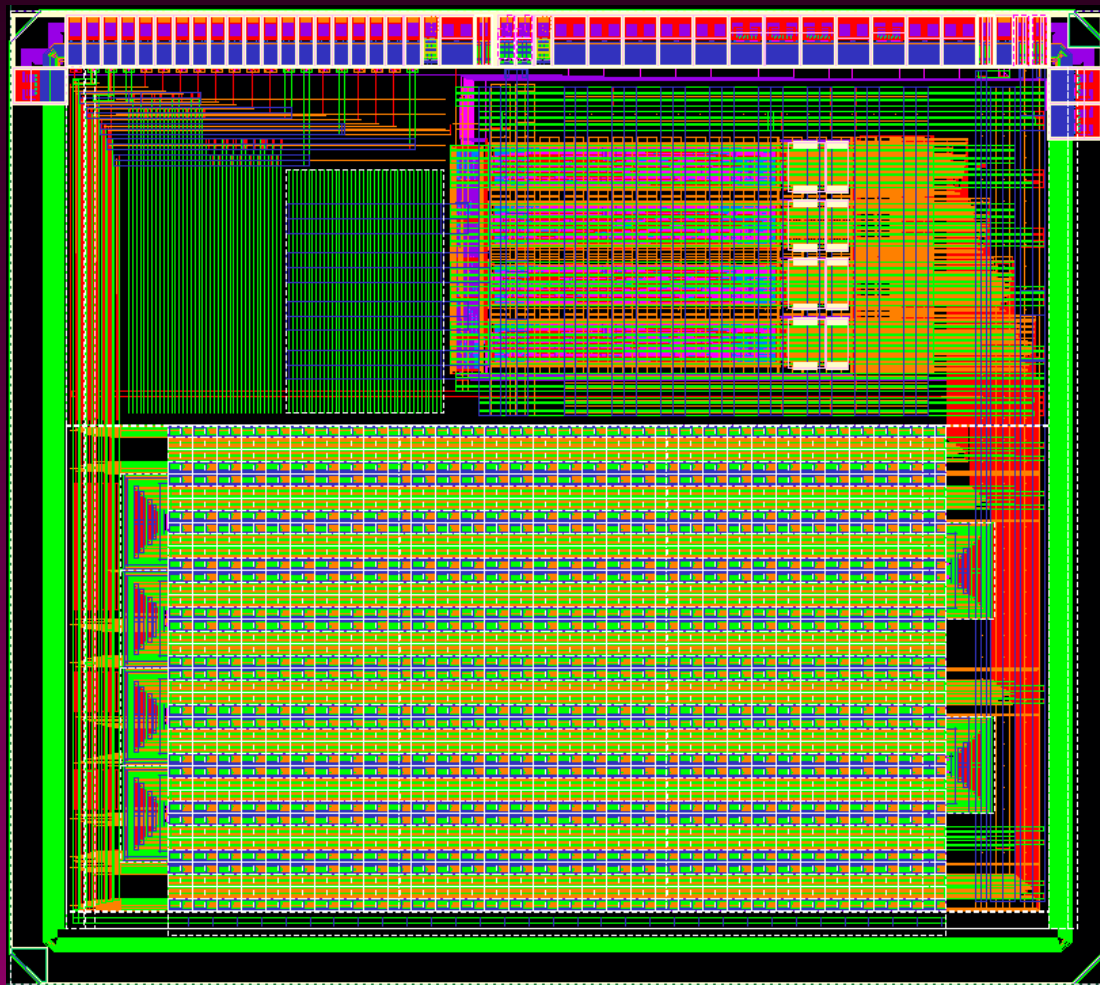
*Common bus*



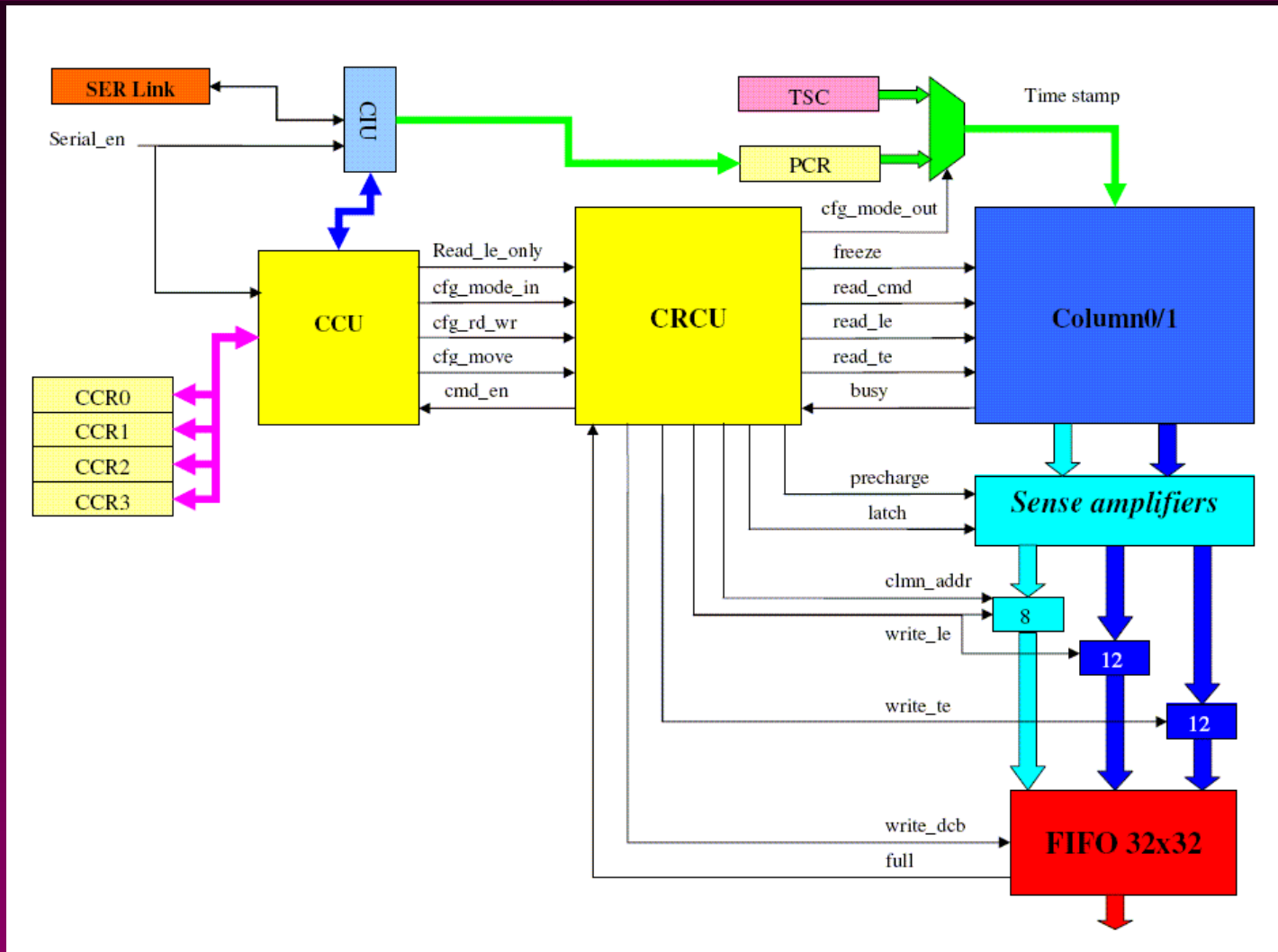
# ToPiX v3 layout



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- \* 4.5 mm × 4 mm
- \* CMOS 130 nm
- \* Clock frequency 160 MHz
- \* bump bonding pads
- \* 2×2×128 columns
- \* 2×2×32 columns
- \* 32 cells EoC FIFO
- \* SEU protected EoC
- \* Serial data output
- \* SLVS I/O







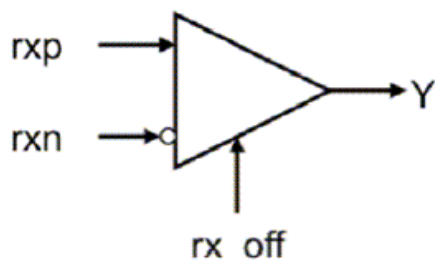
# SLVS



Sezione di Torino

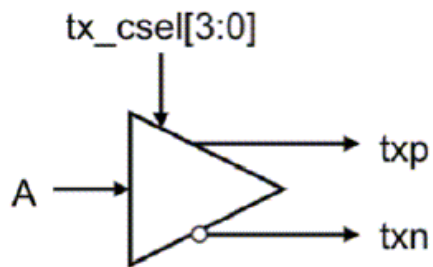
## Receiver

- Power Supply: 1.2V to 1.5V
- Power Dissipation:
  - 150uW @ 320Mbs, 1.2V supply
  - <1uW @ power down



## Driver

- Power Supply: 1.2V to 1.5 V
- Power Dissipation:
  - 3.1mW @ 320Mbs, 1.2 V supply
  - <10uW @ power down



## Engineer

- Sandro Bonacini – CERN, Switzerland

## Electrical Specifications

Symbol	Parameter	Notes	Min	Typ	Max	Units
$V_{OD}$	Differential output voltage		110	200	320	mV
$\Delta V_{OD}$	Differential output voltage change	(fig.1)	0	14	20	mV
$V_{OS}$	Driver offset voltage		100	200	350	mV
$I_{SCO}$	Output short-circuit current	$V_{OS}=0$ , $V_{OD}=0$		-25	-60	mA
$I_{SCOD}$	Differential output short-circuit current	$V_{OD}=0$		-3	-5	mA
$I_{DD}$	Supply current			2.5	4.0	mA

## Programmable Output Current

csel[3:0]	Output current [mA]	Driver power dissipation [mW]
8	2.0	3.0
4	1.3	2.1
2	0.8	1.4
1	0.5	1.0
(sleep) 0	0	<.01

Note: All values are given at 1.2V power supply voltage, typical conditions.

CERN development ( *S. Bonacini* )  
SLVS Driver test with Al cables ongoing

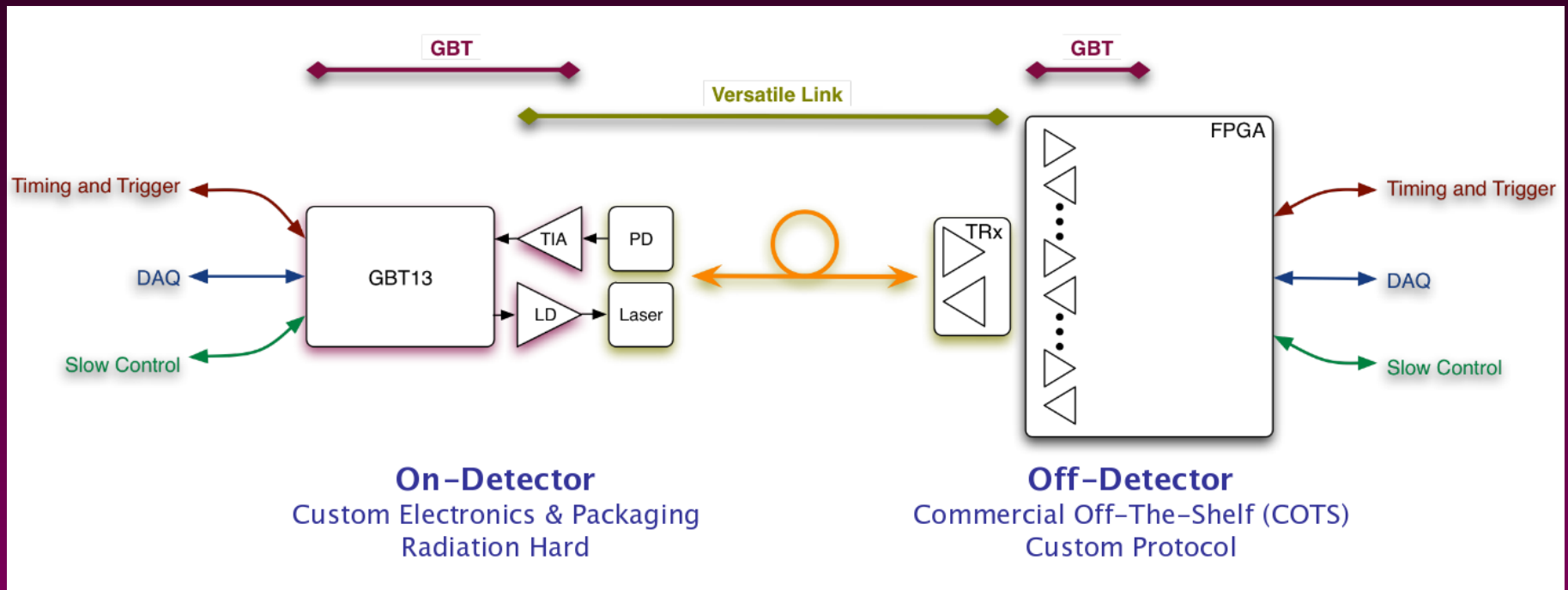




# GBT



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# GBT chipset



## Radiation tolerant chipset :

- \* GBTIA : Transimpedance optical receiver
- \* GBLD : Laser driver
- \* GBTx : Data and Timing Transceiver
- \* GBT-SCA : Slow control ASIC

## Target Applications :

- \* Data readout
- \* TTC
- \* Slow control and monitoring links

## Supports :

- \* Bidirectional data transmission
- \* Bandwidth :
  - Line rate : 4.8 Gb/s
  - Effective : 3.36 Gb/s

## Radiation Tolerance :

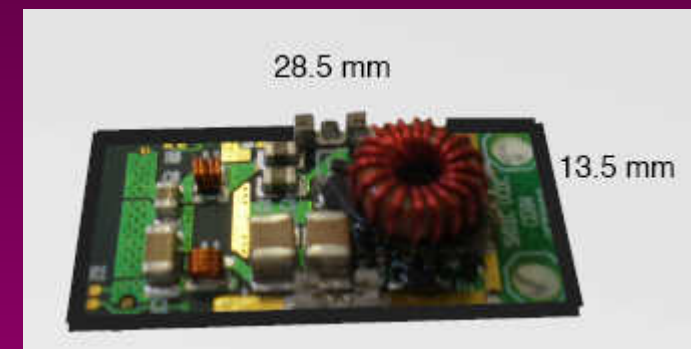
- \* Total dose
- \* Single Event Upset



# Power regulator



- \* ToPiX power supply  $1.2 \text{ V} - I_{\text{DC}} \sim 500 \text{ mA}$  ( estimated )  
→ voltage drop on cables is not negligible
- \* A DC-DC converter solution compatible with the radiation levels and the magnetic field of a silicon tracker is under development @ CERN for sLHC
- \* Current CERN version :  $V_{\text{IN}} 10 \div 12 \text{ V}$ ,  $V_{\text{OUT}} = 1.8 \div 3.3 \text{ V}$ ,  $I_{\text{OUT}} < 3 \text{ A}$
- \*  $V_{\text{OUT}} = 1.2 \text{ V}$  seems feasible
- \* Board position t.b.d.  
→ *ToPiX internal regulator t.b.d.*





# Conclusions



- \* A pixel readout architecture has been defined – waits for more detailed rate simulations to be finalized.
- \* F/E ASIC with full pixel cells and columns has been designed and tested – a new prototype, with full end of column logic has been submitted to foundry.
- \* A GBT-based interface to the DAQ system is under evaluation. Contacts with the CERN GBT group ongoing.
- \* Started discussion with a CERN group for radiation tolerant DC-DC converter. A solution based on the AMIS ASIC is under evaluation.



## Next steps



- \* Test of ToPiX v3 ( *G. Mazza, M. Mignone, A. Rivetti, R. Wheadon* )
- \* Simulations of the ToPiX updated architecture with the data ← input from simulations ( *L. Zotti* )
- \* ToPiX more accurate power estimation ( from v3 tests ) → input to cooling design ( *S. Coli* )
- \* 1<sup>st</sup> approximation definition of the data trasmission board and the power regulator board → input to mechanical design ( *G. Girauda* )
- \* New aluminium cables testing with SLVS drivers ( *P. De Remigis* )
- \* Bump bonding with detector, test beam preparation ( *D. Calvo, M. Mignone, R. Wheadon* )